P-Channel 20-V (D-S) MOSFET

Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

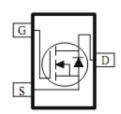
Typical Applications:

- Load Switches
- DC/DC Conversion
- Motor Drives

PRODUCT SUMMARY				
V _{DS} (V)	$r_{DS}(V)$ $r_{DS(on)}(m\Omega)$			
-20	150 @ V _{GS} = -4.5V	-1.3		
	190 @ V _{GS} = -2.5V	-1.1		







ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)						
Parameter				Limit	Units	
Drain-Source Voltage				-20	V	
Gate-Source Voltage				±8	٧	
Continuous Drain Courset a		T _A =25°C	ı	-1.3		
Continuous Drain Current ^a		T _A =70°C	l _D	-1.0	Α	
Pulsed Drain Current ^b				-5	'	
Continuous Source Current (Diode Conduction) a	I _S	-0.5	Α			
Dower Dissipation a		$T_A=25$ °C $T_A=70$ °C	P _D	0.34	W	
Power Dissipation ^a			ı D	0.22	VV	
Operating Junction and Storage Temperature Range				-55 to 150	°C	

THERMAL RESISTANCE RATINGS							
Parameter			Maximum	Units			
Maximum Junction-to-Ambient ^a	t <= 10 sec	$R_{\theta JA}$	375	°C/W			
Maximum Junction-to-Ambient	Steady State	IXOJA	430	C/VV			

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

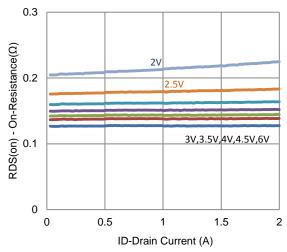
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = -250 \text{ uA}$	-0.4			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			±100	nA	
Zoro Coto Voltago Drain Correct		$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}$			-1 uA		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			-25	uA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	-2.0			Α	
Dania Commo On Bonistono a	r	$V_{GS} = -4.5 \text{ V}, I_D = -1 \text{ A}$			150	mΩ	
Drain-Source On-Resistance ^a	r _{DS(on)}	$V_{GS} = -2.5 \text{ V}, I_D = -0.8 \text{ A}$			190	11177	
Forward Transconductance ^a	g _{fs}	$V_{DS} = -15 \text{ V}, I_{D} = -1 \text{ A}$		4		S	
Diode Forward Voltage ^a	V_{SD}	$I_S = -0.3 \text{ A}, V_{GS} = 0 \text{ V}$		-0.72		V	
		Dynamic ^b					
Total Gate Charge	Q_g	$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V},$		3.7		nC	
Gate-Source Charge	Q_{gs}	$I_{D} = -10 \text{ V}, V_{GS} = -4.3 \text{ V},$		0.6			
Gate-Drain Charge	Q_gd	1D = 174		0.9			
Turn-On Delay Time	t _{d(on)}	$V_{DS} = -10 \text{ V}, R_1 = 10 \Omega,$		7			
Rise Time	t _r	$V_{DS} = -10 \text{ V}, \text{ K}_{L} - 10 \Omega,$ $I_{D} = -1 \text{ A},$		9		ns	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = -4.5 \text{ V}, R_{GEN} = 6 \Omega$		26			
Fall Time	t _f	V GEN = 4.5 V, T GEN = 0 12		13			
Input Capacitance	C _{iss}			216			
Output Capacitance	C _{oss}	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		29		pF	
Reverse Transfer Capacitance	C _{rss}			24			

Notes

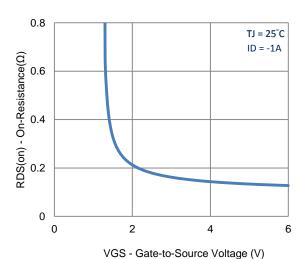
- Pulse test: PW <= 300us duty cycle <= 2%.
- Guaranteed by design, not subject to production testing. b.

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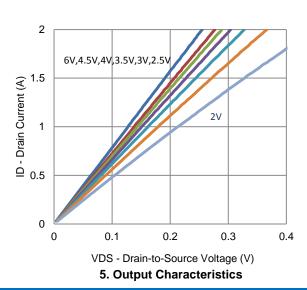
Typical Electrical Characteristics



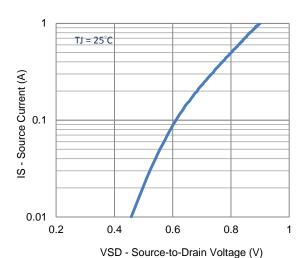
1. On-Resistance vs. Drain Current



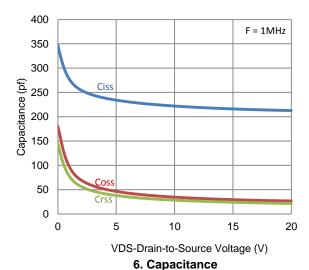
3. On-Resistance vs. Gate-to-Source Voltage



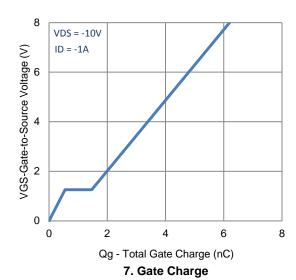
2. Transfer Characteristics

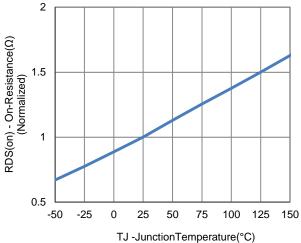


4. Drain-to-Source Forward Voltage

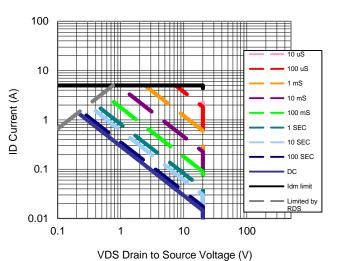


Typical Electrical Characteristics

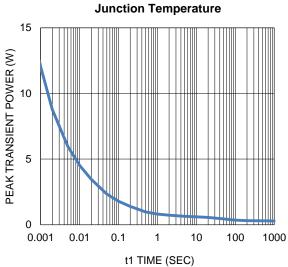




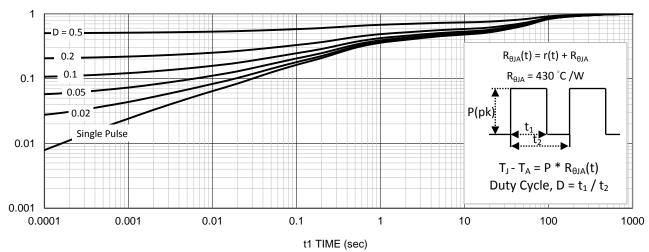
8. Normalized On-Resistance Vs



9. Safe Operating Area

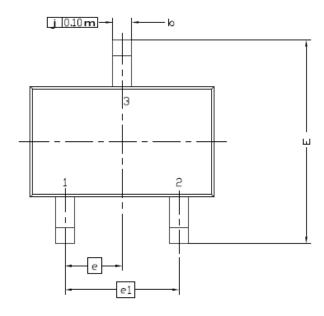


10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

Package Information



DIM.	MILLIMETERS			INCHES			
DIM	MIN	NDM	MAX	MIN	NDM	MAX	
Α	0,900	0,95	1,10	0,035	0,037	0.043	
A1	0.00		0.10	0.000		0.004	
A2	0.70	0.90	1.00	0.028	0.035	0.039	
b	0.15	0.22	0.30	0.006	0.016	0.012	
С	0.08	0.127	0.20	0.003	0.003 0.005		
D	210 BSC			0.083 BSC			
Ε	2.30 BSC			0.091 BSC			
E1	1,30 BSC			0.051 BSC			
6	0.65 BSC			0.026 BSC			
e1	1,30 BSC 0,051 BSC			C			
L	0.26	0.40	0.46	0.010	0,015	0.018	
L2	0.254BSC			0.010BSC			
R	0.10			0,004			
θ	0°	4°	8°	0°	4°	8*	
θ1		7°NDM 7°NDM					

